10-E106PMA020SA-L925A38Z
datasheet

Vincotech

*flow*PIM E1 — 600 V / 20 A

Topology features

- Open Emitter configuration
- Temperature sensor
- Converter+Brake+Inverter

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Solder pin

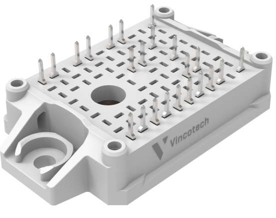
Target applications

- Industrial Drives

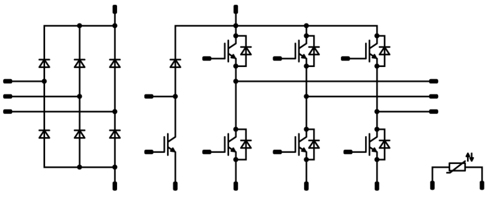
Types

- 10-E106PMA020SA-L925A38Z

flow E1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	28	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	66	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 360 V	T_j = 150 °C	6	μs
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	28	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	50	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter voltage	V_{CES}			600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	28	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	66	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 360 V	T_j = 150 °C	6	μs
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Brake Diode					
Peak repetitive reverse voltage	V_{RRM}			600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s <= 80 °C	20 (1)	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	41	W
Maximum junction temperature	T_{jmax}			175	°C

(1) limited by I_{FRM}

Parameter	Symbol	Conditions		Value	Unit
Rectifier Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	47	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	270	A
Surge current capability	I^2t			370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	61	W
Maximum junction temperature	T_{jmax}			150	°C

Module Properties

Parameter	Symbol	Conditions		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Typ	Max	Unit
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00029	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		20	25 125	1,1	1,55 1,75	1,9(2)	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,1	μA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1100		pF
Output capacitance	C_{oes}							71		pF
Reverse transfer capacitance	C_{res}							32		pF
Gate charge	Q_g	V_{CC} = 480 V	0/15		20	25		120		nC
Thermal										
Thermal resistance junction to sink(3)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,44		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	20	25 125 150		67,2 66,2 66,2		ns
Rise time	t_r					25 125 150		26 27,2 28		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		115,8 133,8 137,6		ns
Fall time	t_f					25 125 150		69,11 87,03 88,48		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,87 μC Q_{rFWD}=1,64 μC Q_{rFWD}=1,91 μC				25 125 150		0,45 0,624 0,677		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,426 0,578 0,613		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				20	25 125 150	1,25	1,7 1,58 1,58	1,95(2)	V
Reverse leakage current	I_R	V_r = 600 V				25			27	μA
Thermal										
Thermal resistance junction to sink(3)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,91		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=759 A/μs di/dt=802 A/μs di/dt=896 A/μs	±15	350	20	25 125 150		8,88 11,5 12,4		A
Reverse recovery time	t_{rr}					25 125 150		229,09 306,28 325,67		ns
Recovered charge	Q_r					25 125 150		0,87 1,64 1,91		μC
Reverse recovered energy	E_{rec}					25 125 150		0,221 0,407 0,477		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		38,26 81,03 82,44		A/μs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00029	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		20	25 125	1,1	1,55 1,75	1,9(2)	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,1	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1100		pF
Output capacitance	C_{oes}							71		pF
Reverse transfer capacitance	C_{res}							32		pF
Gate charge	Q_g	V_{CC} = 480 V	0/15		20	25		120		nC
Thermal										
Thermal resistance junction to sink(3)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,44		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	0/15	400	20	25 125 150		15,8 15,2 15,6		ns
Rise time	t_r					25 125 150		12,2 14 14,8		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		153,8 169 173,6		ns
Fall time	t_f					25 125 150		68,05 79,29 89,65		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,699 µC Q_{rFWD}=1,37 µC Q_{rFWD}=1,52 µC				25 125 150		0,358 0,555 0,595		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,494 0,708 0,749		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				10	25 125	1,25	1,58 1,52	1,95(2)	V
Reverse leakage current	I_R	V_r = 600 V				25			27	µA
Thermal										
Thermal resistance junction to sink(3)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,33		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=1281 A/µs di/dt=726 A/µs di/dt=725 A/µs	0/15	400	20	25 125 150		10,72 10,6 11,21		A
Reverse recovery time	t_{rr}					25 125 150		192,6 296,88 323,43		ns
Recovered charge	Q_r					25 125 150		0,699 1,37 1,52		µC
Reverse recovered energy	E_{rec}					25 125 150		0,203 0,404 0,447		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		1655 32,85 33,98		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Static										
Forward voltage	V_F				5	25 125		0,901 0,78	1,1[(2)]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink[(3)]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,15		K/W
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 493 Ω				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %						3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %						3437		K
Vincotech Thermistor Reference									K	

(2) Value at chip level

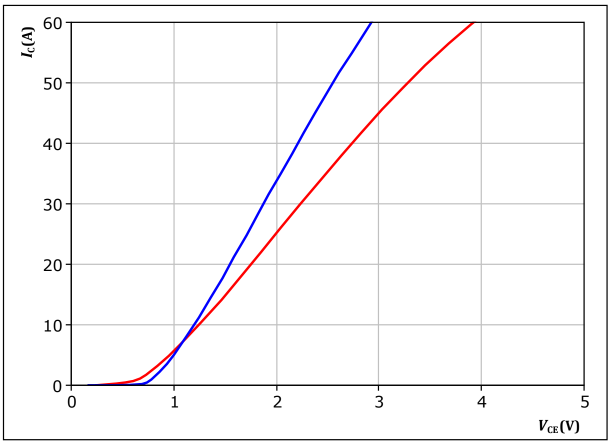
(3) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

I_C = f(V_{CE})

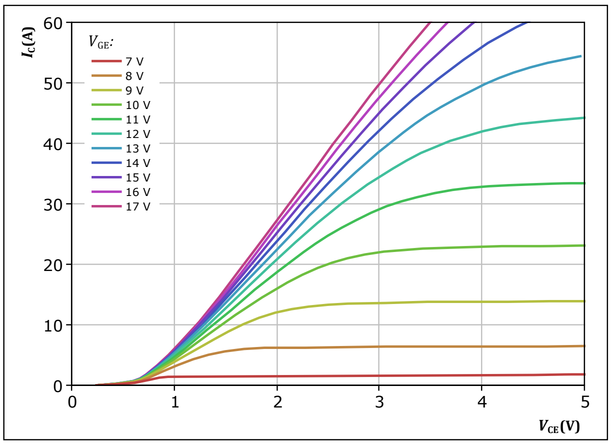


t_p = 250 µs
V_{GE} = 15 V
T_j: 25 °C, 125 °C

figure 2. IGBT

Typical output characteristics

I_C = f(V_{CE})

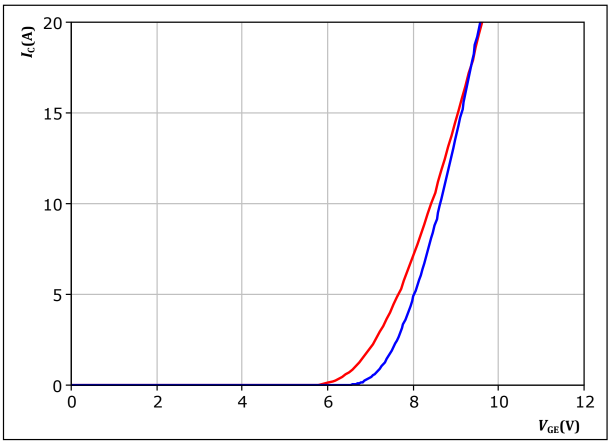


t_p = 250 µs
T_j = 125 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

I_C = f(V_{GE})

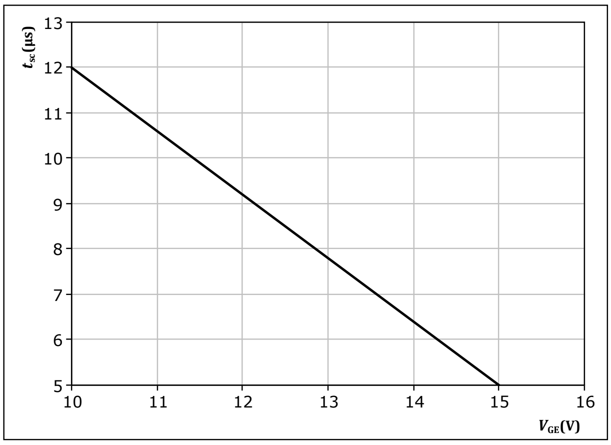


t_p = 250 µs
V_{CE} = 10 V
T_j: 25 °C, 125 °C

figure 4. IGBT

Short circuit withstand time as a function of V_{GE}

t_{sc} = f(V_{GE})



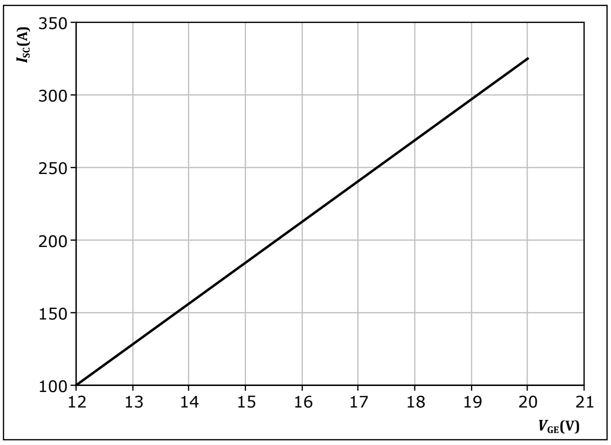
At V_{CE} = 333 V
T_j ≤ 333 °C

Inverter Switch Characteristics

figure 5. **IGBT**

Typical short circuit current as a function of V_{GE}

I_{SC} = f(V_{GE})

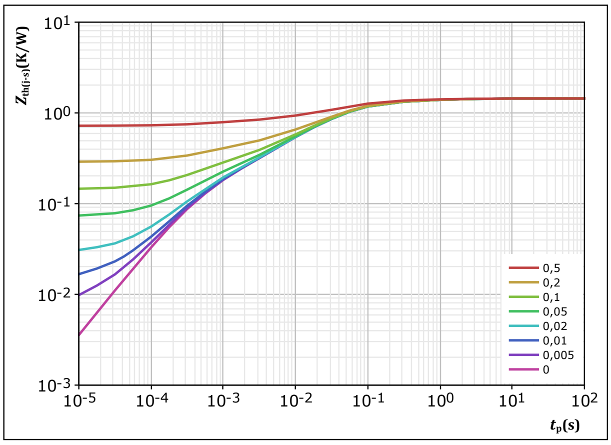


At	V_{CE} =	333	V
	T_j ≤	333	°C

figure 6. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,442 K/W

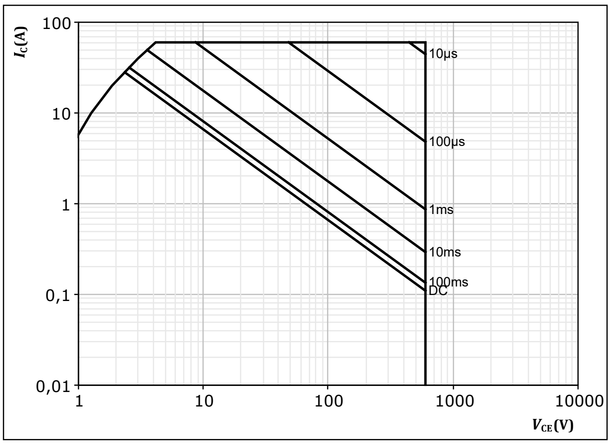
IGBT thermal model values

R (K/W)	τ (s)
7,44E-02	1,94E+00
1,73E-01	2,52E-01
6,82E-01	4,62E-02
2,86E-01	1,04E-02
1,12E-01	2,50E-03
1,15E-01	4,24E-04

figure 7. **IGBT**

Safe operating area

I_C = f(V_{CE})



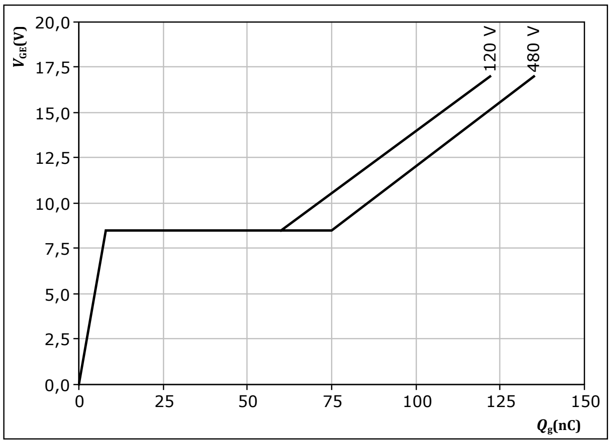
D = single pulse

T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 8. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



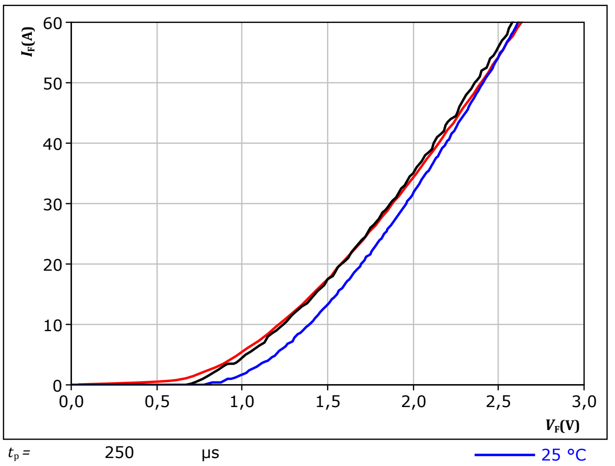
I_C =	33	A
T_j =	25	°C

Inverter Diode Characteristics

figure 9. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



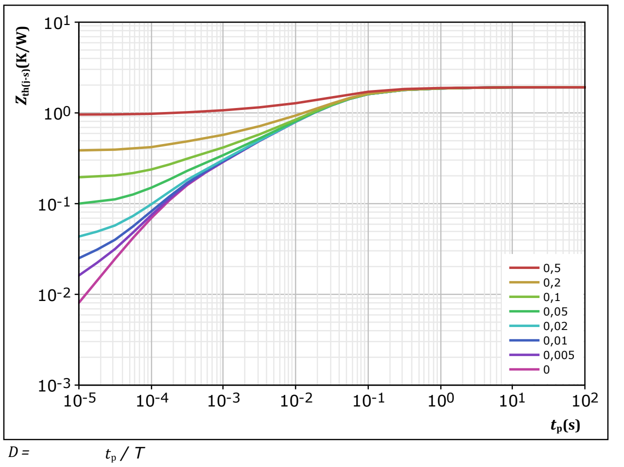
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 10. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,914 K/W

FWD thermal model values

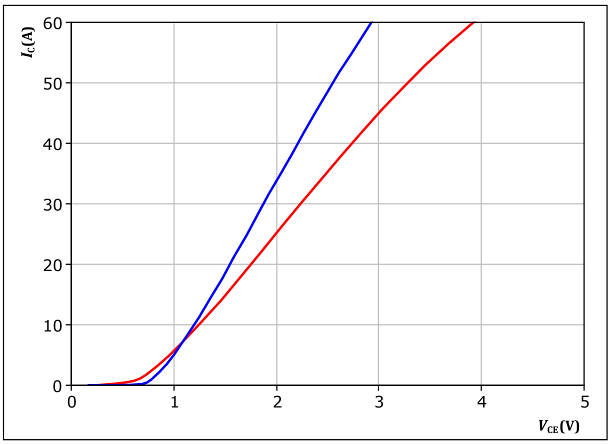
R (K/W)	τ (s)
8,07E-02	2,21E+00
2,18E-01	2,22E-01
8,50E-01	4,41E-02
4,32E-01	9,35E-03
2,00E-01	1,60E-03
1,34E-01	2,12E-04

Brake Switch Characteristics

figure 11. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



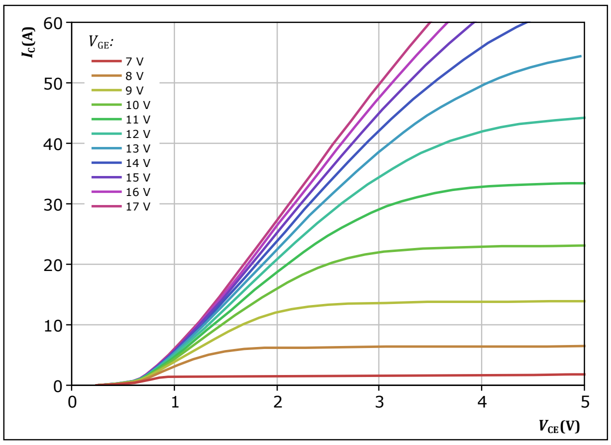
t_p =	250	μs
V_{GE} =	15	V

T_j: 25 °C, 125 °C

figure 12. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



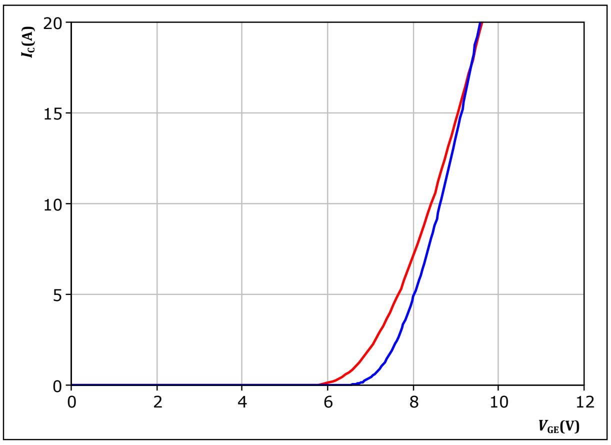
t_p =	250	μs
T_j =	125	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 13. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



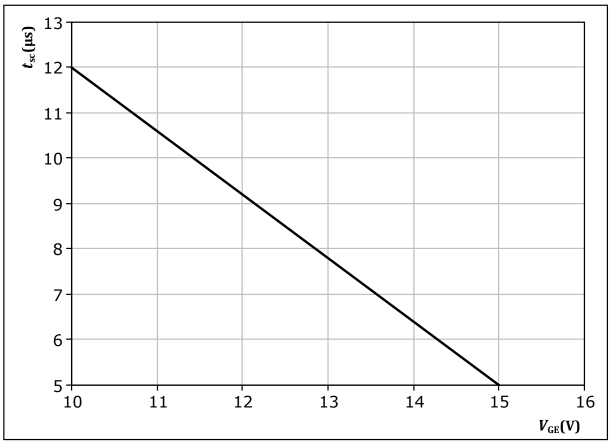
t_p =	250	μs
V_{CE} =	10	V

T_j: 25 °C, 125 °C

figure 14. **IGBT**

Short circuit withstand time as a function of V_{GE}

t_{sc} = f(V_{GE})



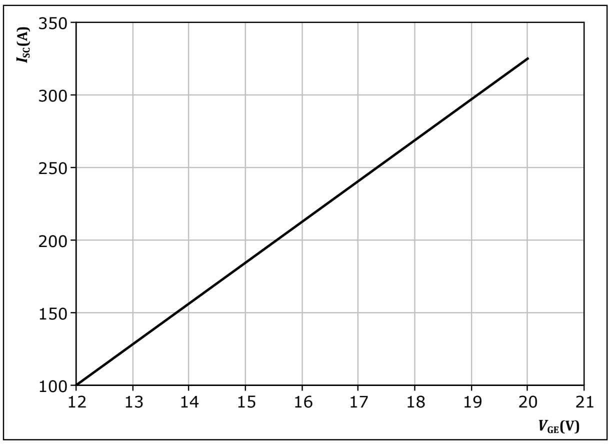
At	V_{CE} =	333	V
	T_j ≤	333	°C

Brake Switch Characteristics

figure 15. IGBT

Typical short circuit current as a function of V_{GE}

I_{SC} = f(V_{GE})

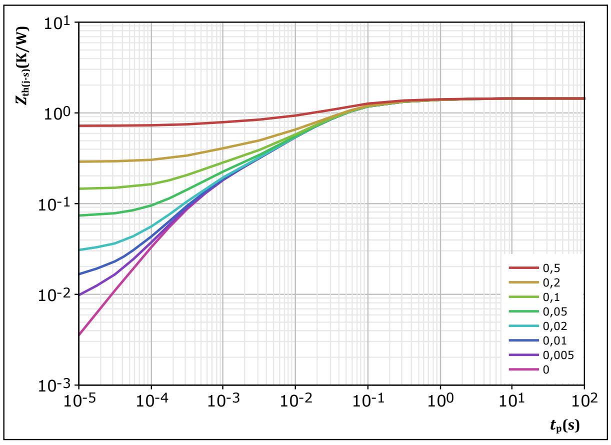


At	V_{CE} =	333	V
	T_j ≤	333	°C

figure 16. IGBT

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,442 K/W

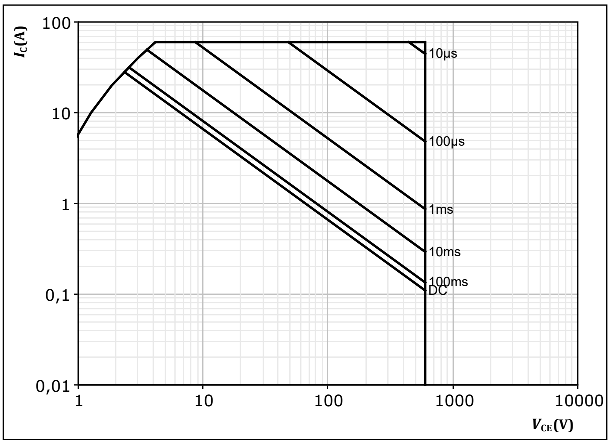
IGBT thermal model values

R (K/W)	τ (s)
7,44E-02	1,94E+00
1,73E-01	2,52E-01
6,82E-01	4,62E-02
2,86E-01	1,04E-02
1,12E-01	2,50E-03
1,15E-01	4,24E-04

figure 17. IGBT

Safe operating area

I_C = f(V_{CE})

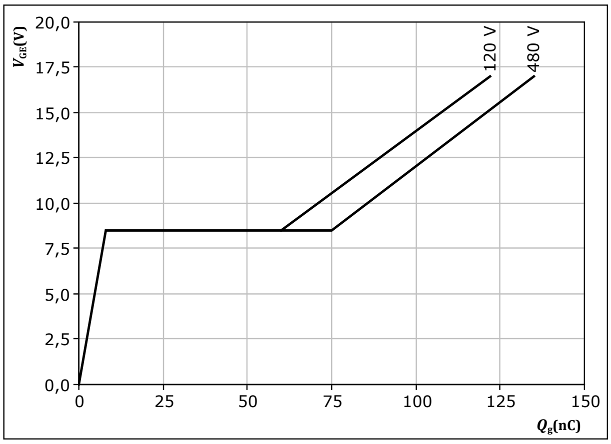


D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 18. IGBT

Gate voltage vs gate charge

V_{GE} = f(Q_g)



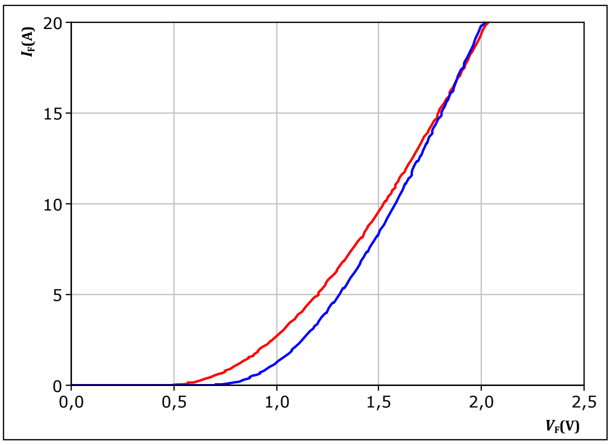
I_C =	33	A
T_j =	25	°C

Brake Diode Characteristics

figure 19. **FWD**

Typical forward characteristics

I_F = f(V_F)



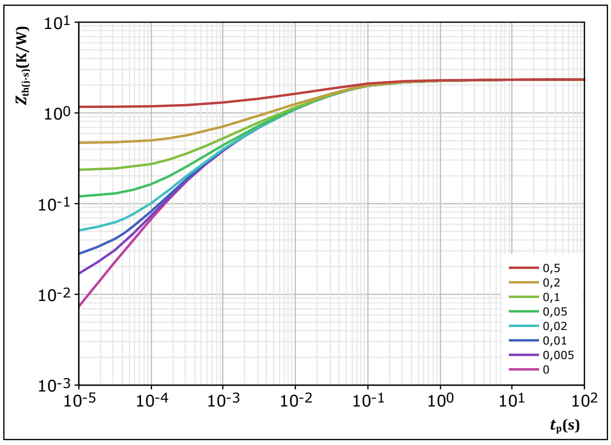
t_p = 250 µs

T_j: 25 °C, 125 °C

figure 20. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,328 K/W

FWD thermal model values

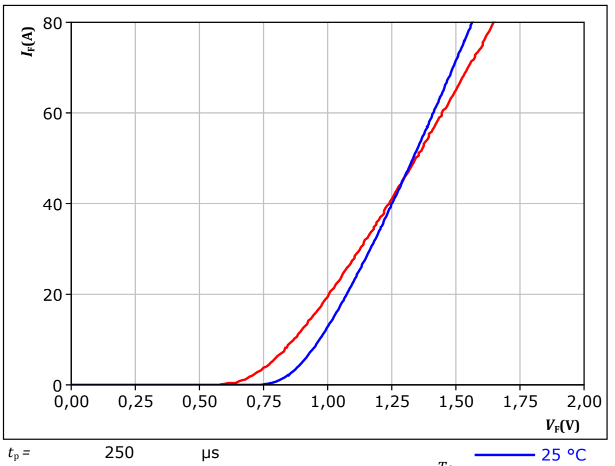
R (K/W)	τ (s)
8,21E-02	3,78E+00
2,22E-01	2,71E-01
9,31E-01	4,55E-02
5,61E-01	8,74E-03
3,70E-01	1,93E-03
1,62E-01	3,48E-04

Rectifier Diode Characteristics

figure 21. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



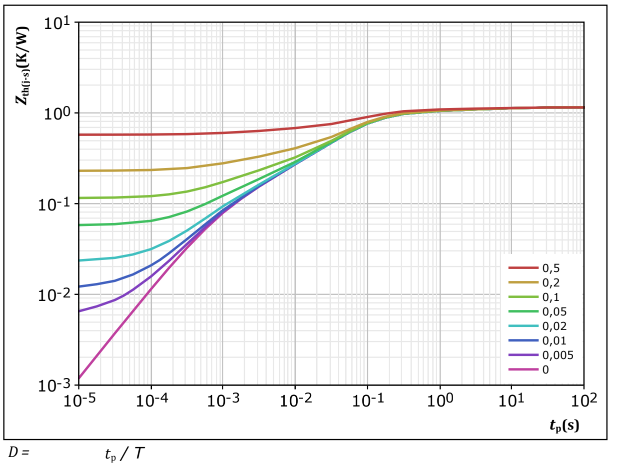
t_p = 250 µs

T_j: 25 °C, 125 °C

figure 22. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,149 K/W

Rectifier thermal model values

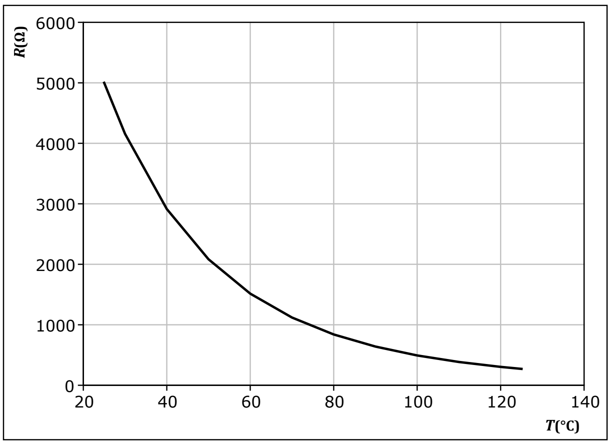
R (K/W)	τ (s)
8,29E-02	7,59E+00
1,02E-01	6,72E-01
4,20E-01	1,19E-01
3,78E-01	4,22E-02
1,08E-01	4,04E-03
5,78E-02	7,21E-04

Thermistor Characteristics

figure 23. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

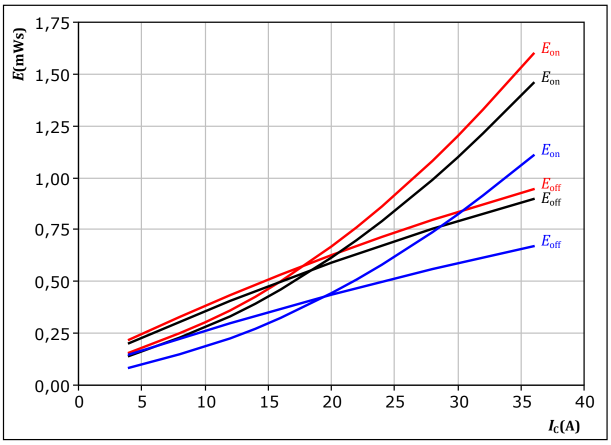


Inverter Switching Characteristics

figure 24. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

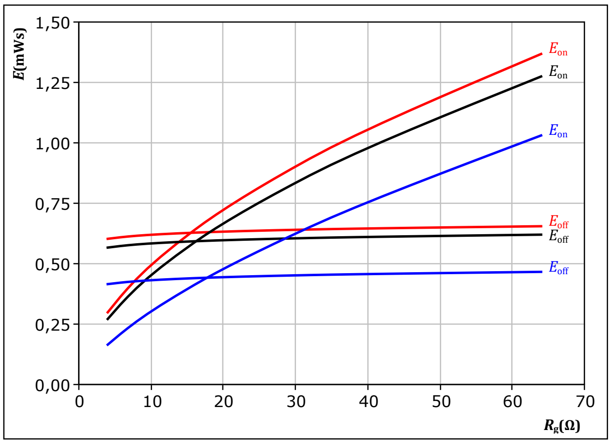
V_{CE} =	350	V	
V_{GE} =	±15	V	
R_{gon} =	16	Ω	
R_{goff} =	16	Ω	

T_j: 25 °C, 125 °C, 150 °C

figure 25. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



With an inductive load at

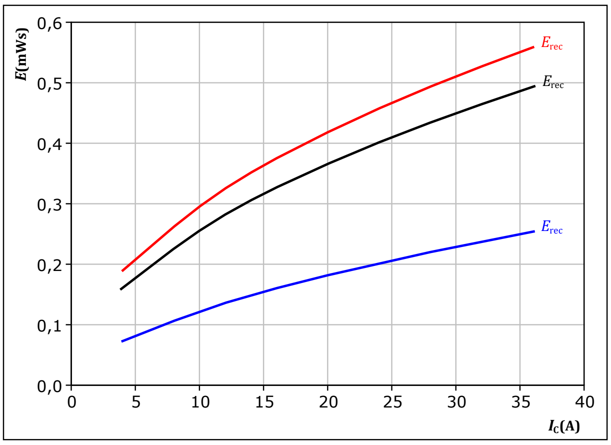
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	20	A

T_j: 25 °C, 125 °C, 150 °C

figure 26. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

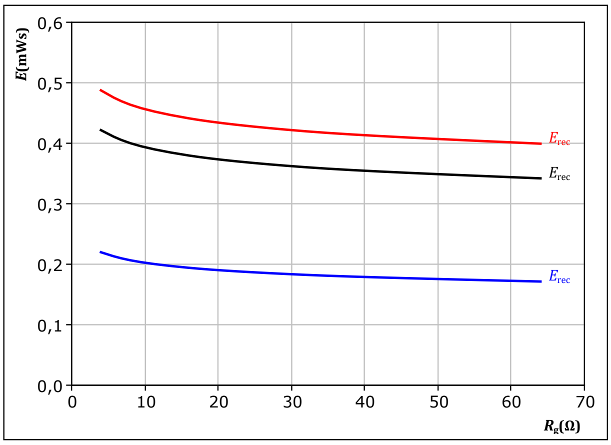
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 27. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	20	A

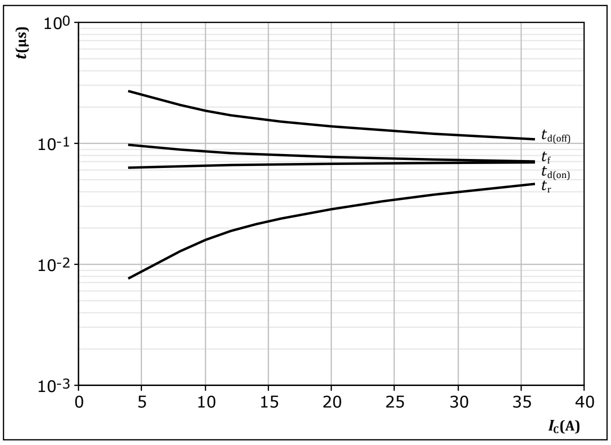
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 28. IGBT

Typical switching times as a function of collector current

t = f(I_C)



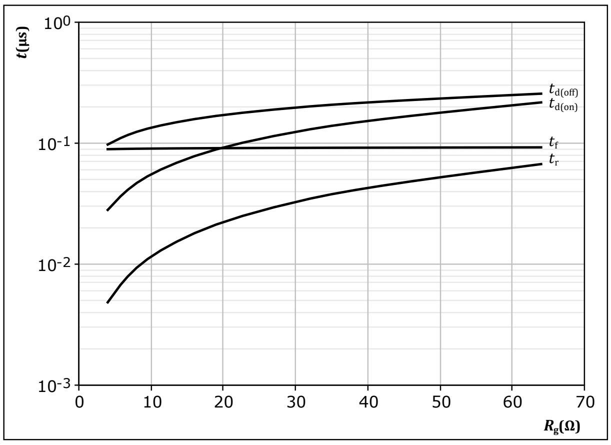
With an inductive load at

T_j =	150	°C
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 29. IGBT

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



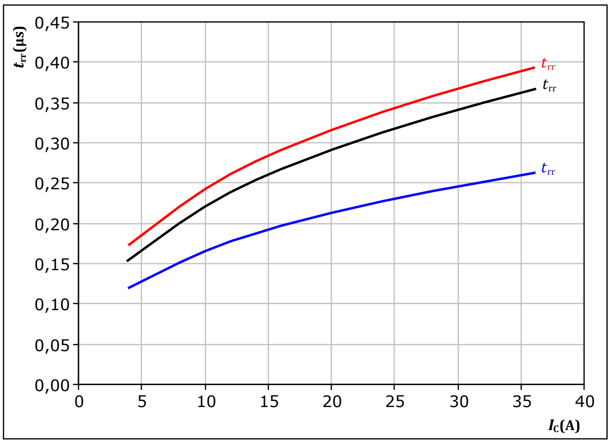
With an inductive load at

T_j =	150	°C
V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	20	A

figure 30. FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

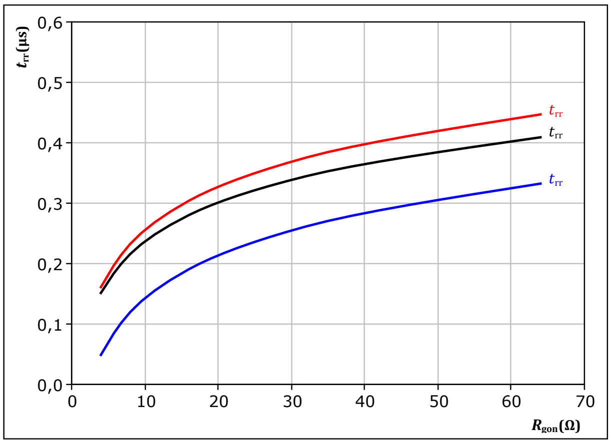
V_{CE} =	350	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 31. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	350	V
V_{GE} =	±15	V
I_C =	20	A

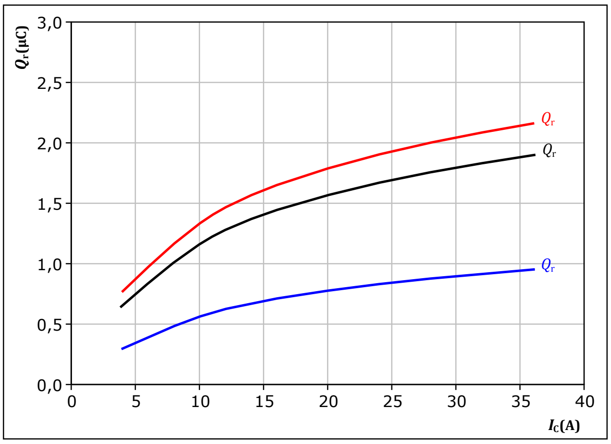
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 32. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



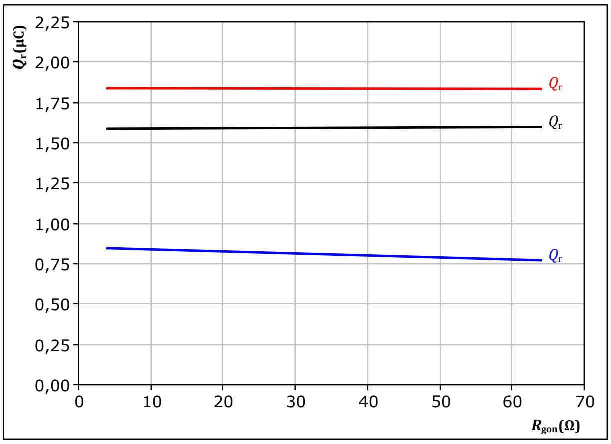
With an inductive load at

V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 33. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



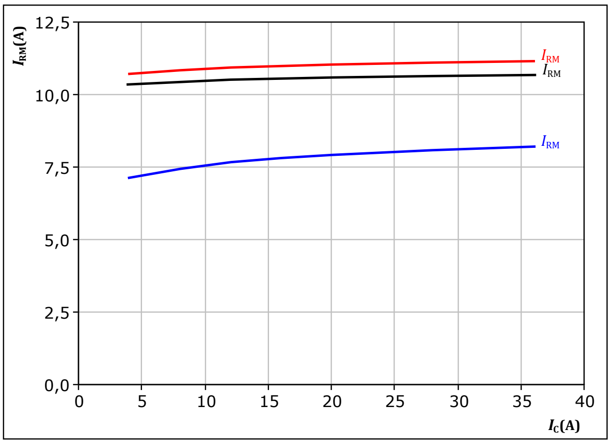
With an inductive load at

V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	20	A		150 °C

figure 34. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



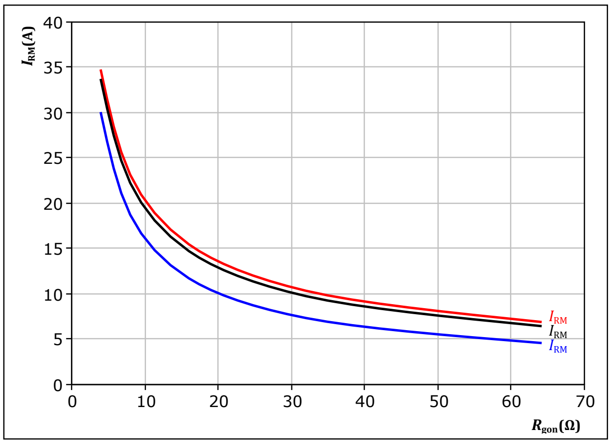
With an inductive load at

V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 35. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

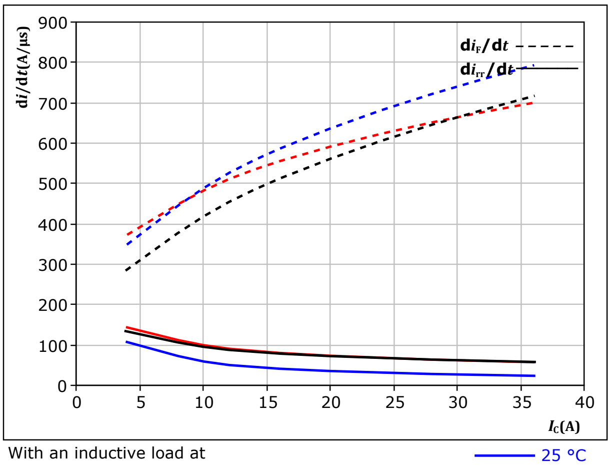
V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	20	A		150 °C

Inverter Switching Characteristics

figure 36. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



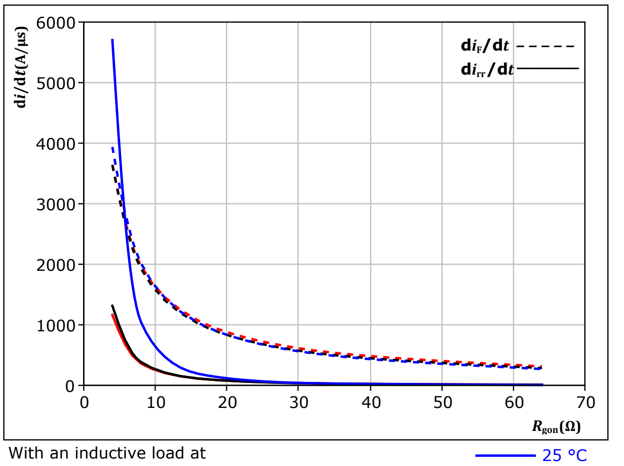
With an inductive load at

V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 37. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



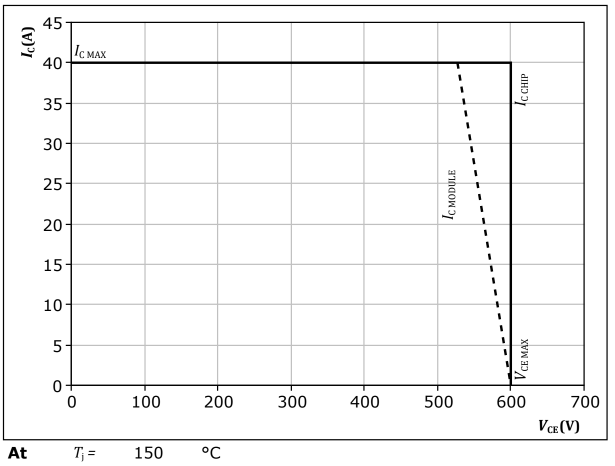
With an inductive load at

V_{CE} =	350	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	20	A		150 °C

figure 38. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



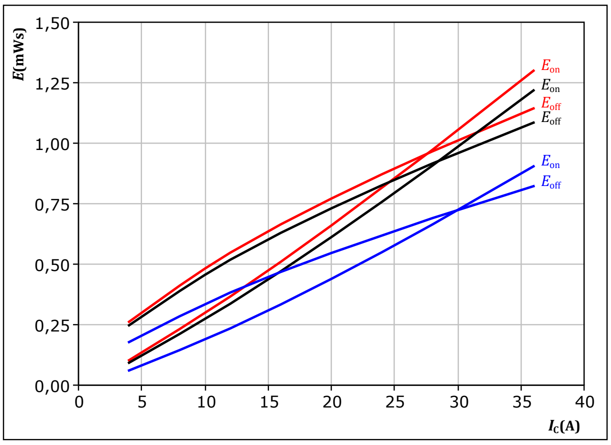
At	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Brake Switching Characteristics

figure 39. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



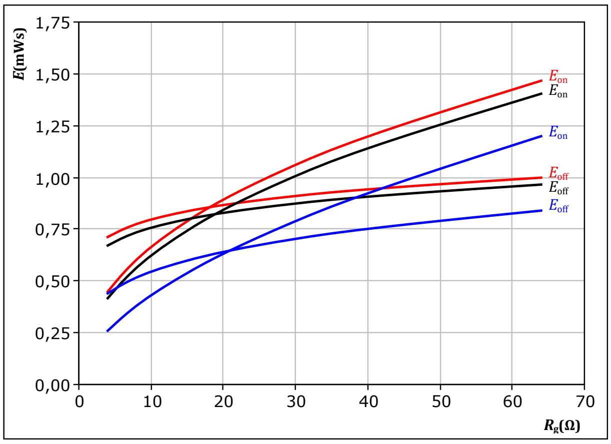
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C
R_{goff} =	8	Ω		

figure 40. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



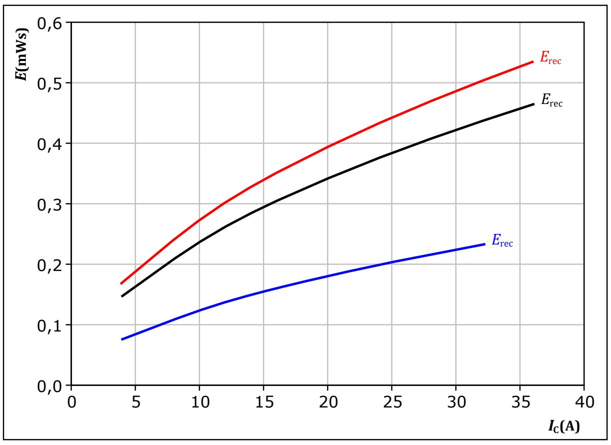
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	20	A		150 °C

figure 41. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



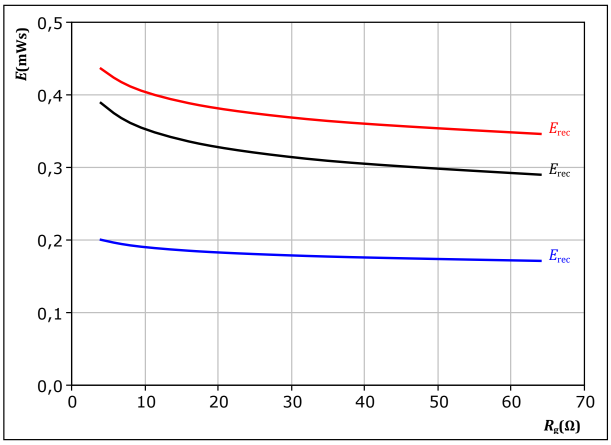
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 42. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

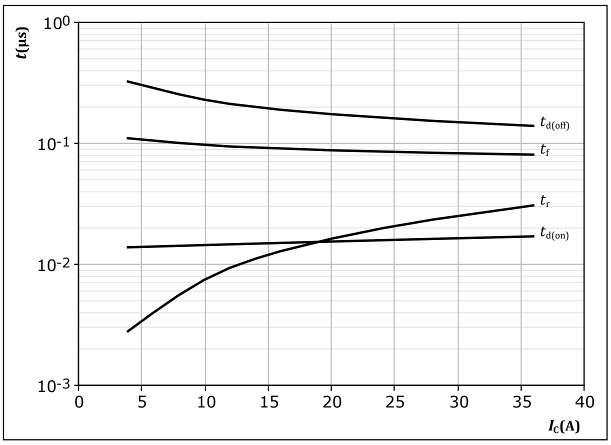
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	20	A		150 °C

Brake Switching Characteristics

figure 43.	IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



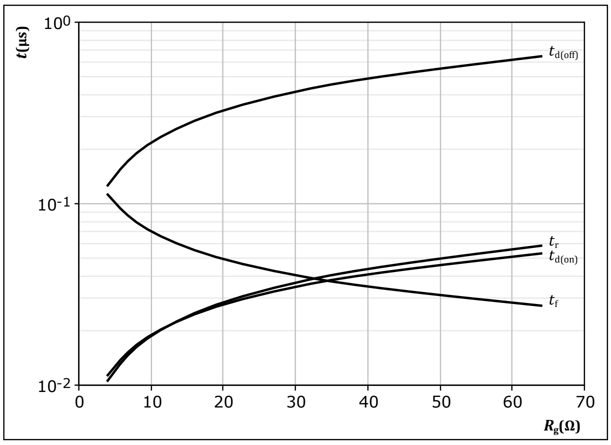
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 44.	IGBT

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



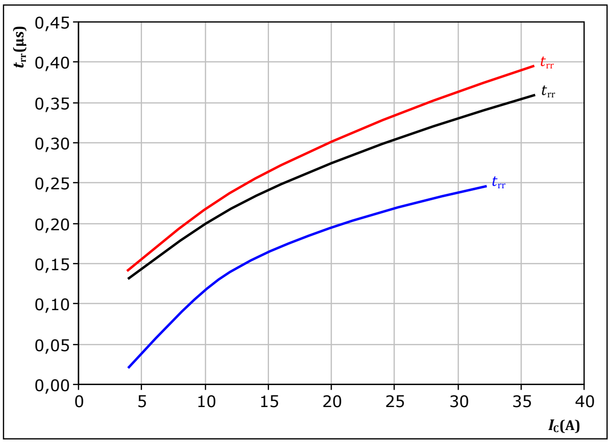
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	20	A

figure 45.	FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

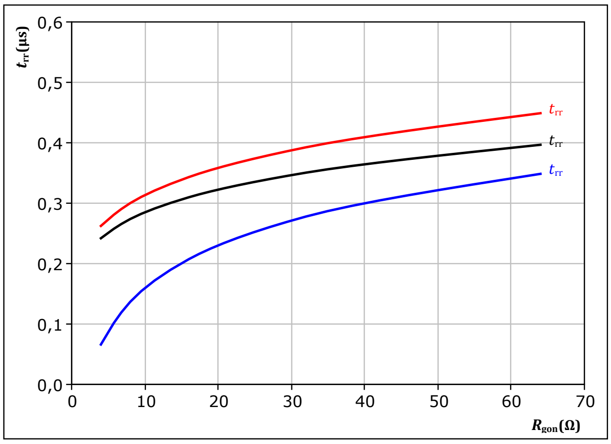
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 46.	FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	20	A

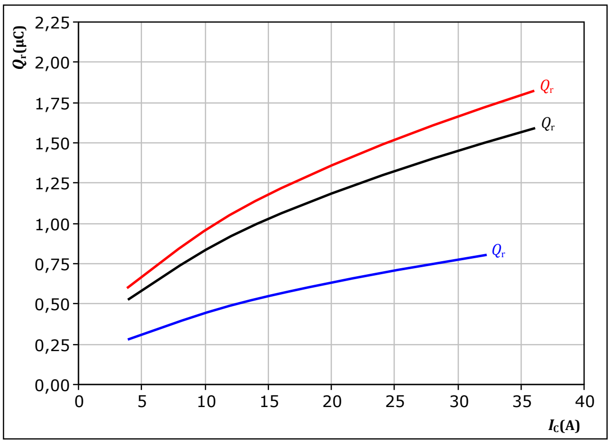
T_j: 25 °C, 125 °C, 150 °C

Brake Switching Characteristics

figure 47. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



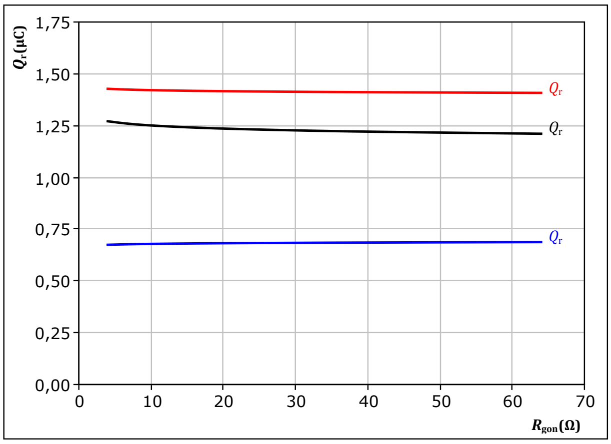
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 48. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



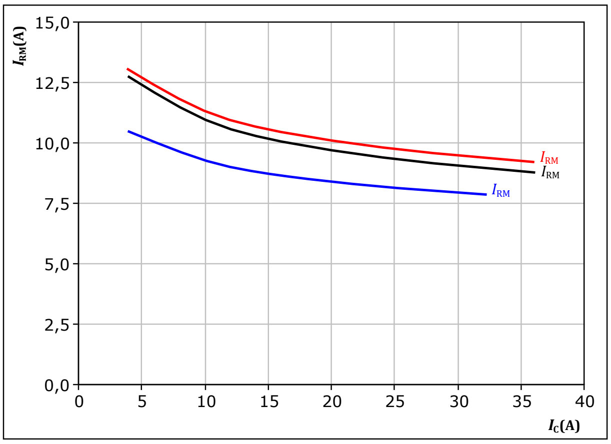
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	20	A		150 °C

figure 49. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



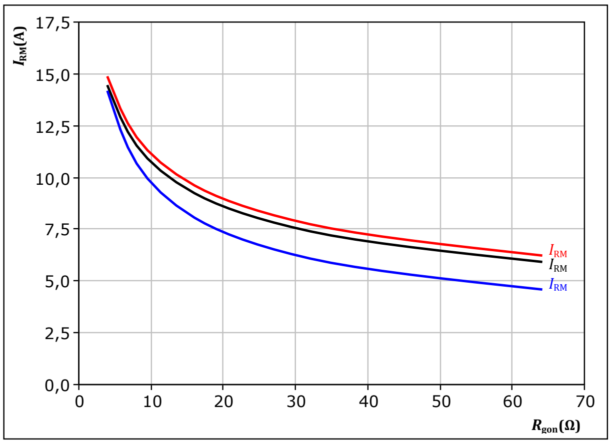
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 50. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

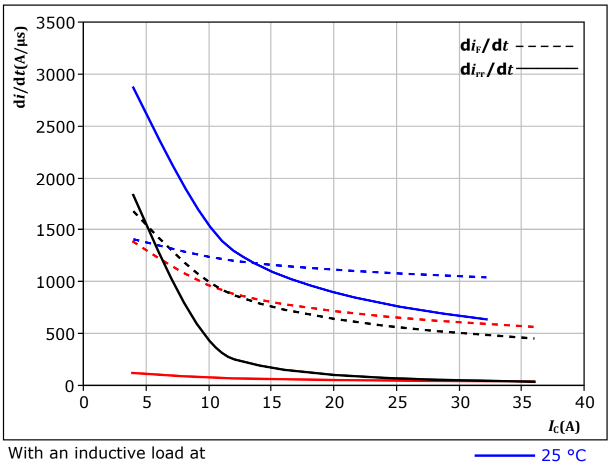
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	20	A		150 °C

Brake Switching Characteristics

figure 51. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



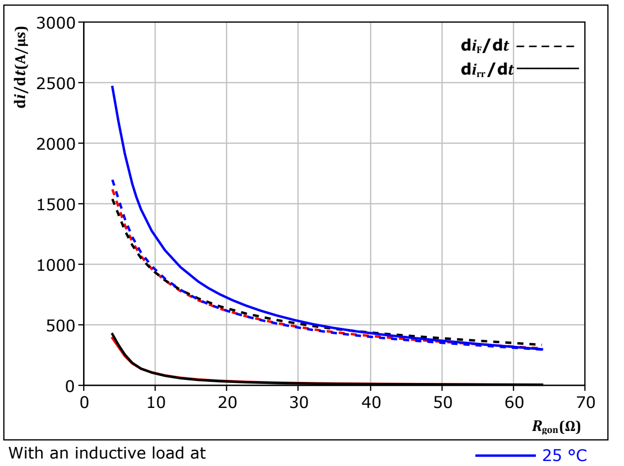
With an inductive load at

V_{CE} =	400	V	
V_{GE} =	0/15	V	T_j: 25 °C / 125 °C / 150 °C
R_{gon} =	8	Ω	

figure 52. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



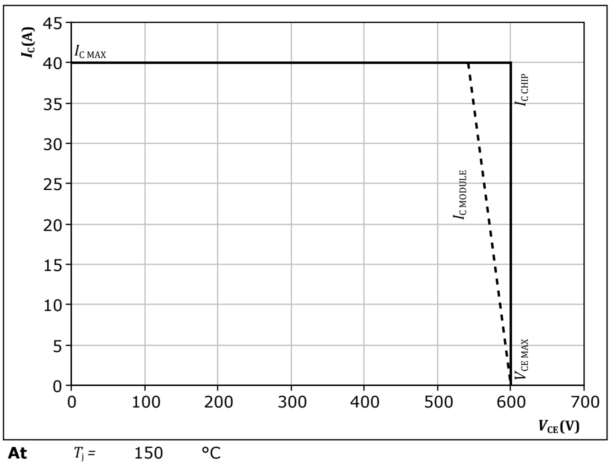
With an inductive load at

V_{CE} =	400	V	
V_{GE} =	0/15	V	T_j: 25 °C / 125 °C / 150 °C
I_C =	20	A	

figure 53. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	8	Ω
	R_{goff} =	8	Ω

Switching Definitions

figure 54. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

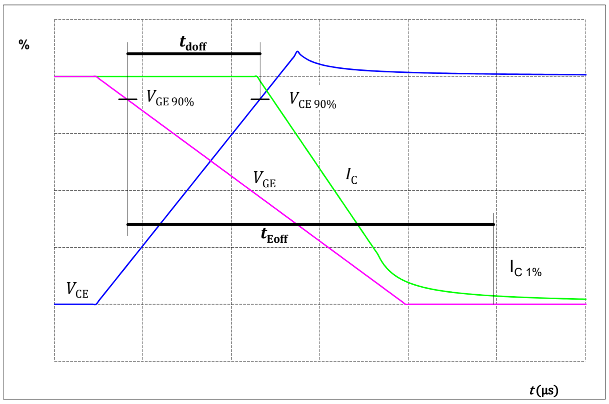


figure 55. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

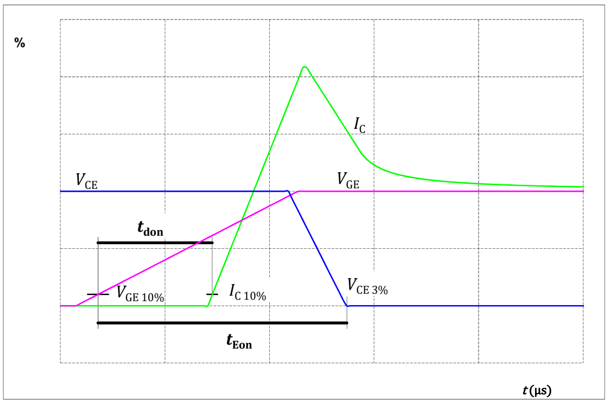


figure 56. **IGBT**

Turn-off Switching Waveforms & definition of t_f

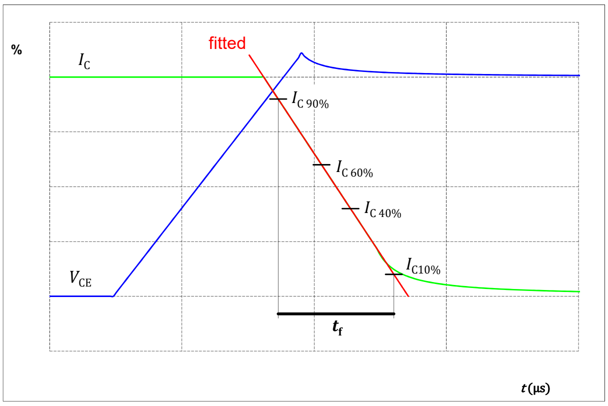
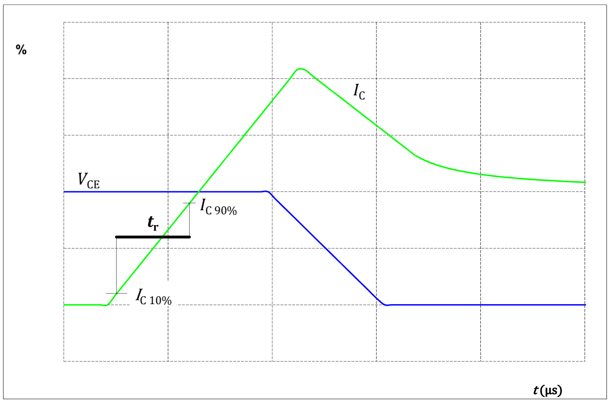


figure 57. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 58. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

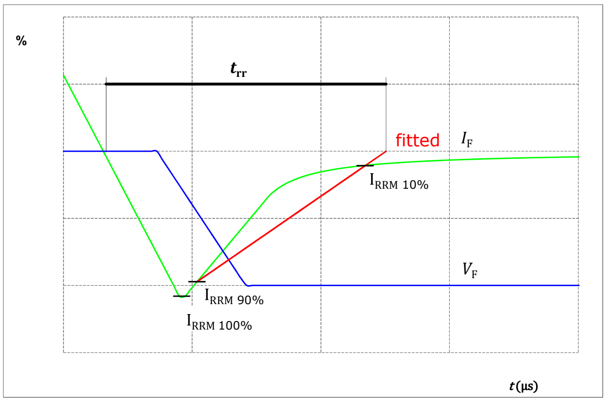
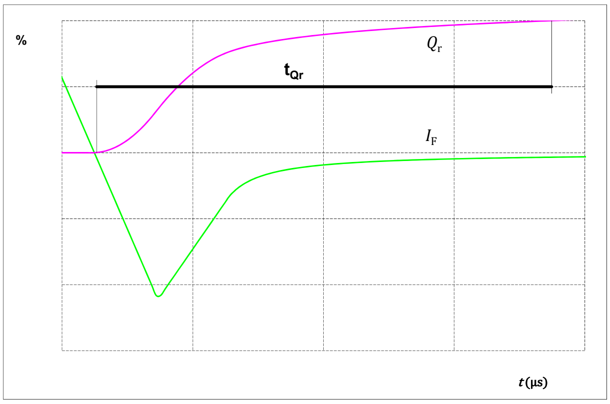


figure 59. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

Version	Ordering Code
Without thermal paste	10-E106PMA020SA-L925A38Z
With thermal paste (3,4 W/mK, PSX-P7)	10-E106PMA020SA-L925A38Z-/3/

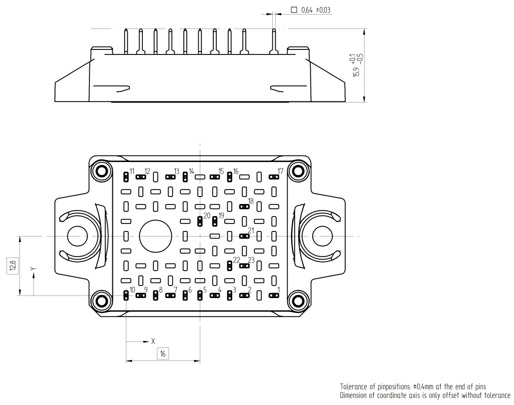
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

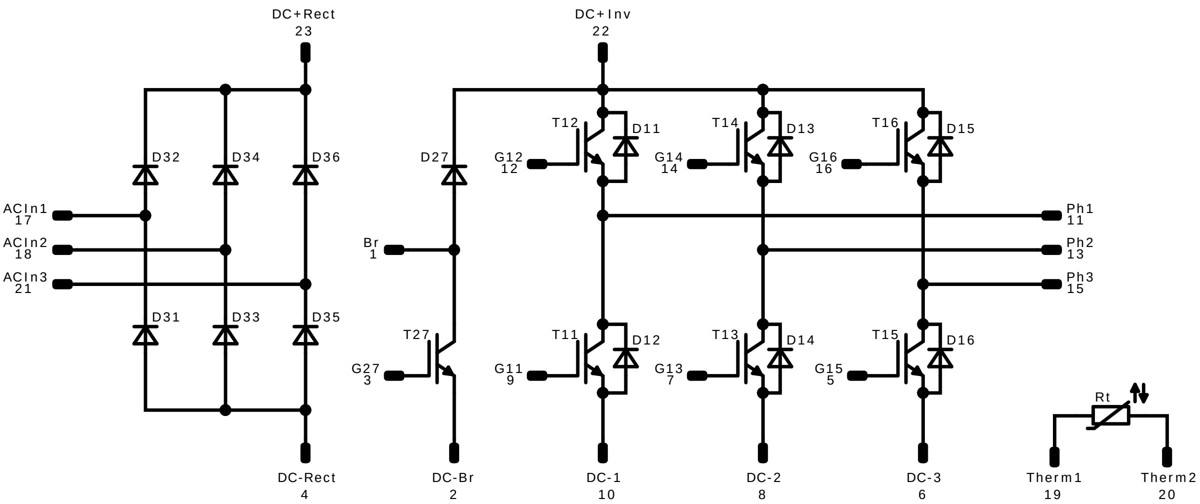
Outline

Pin table [mm]

Pin	X	Y	Function
1	32	0	Br
2	25,6	0	DC-Br
3	22,4	0	G27
4	19,2	0	DC-Rect
5	16	0	G15
6	12,8	0	DC-3
7	9,6	0	G13
8	6,4	0	DC-2
9	3,2	0	G11
10	0	0	DC-1
11	0	25,6	Ph1
12	3,2	25,6	G12
13	9,6	25,6	Ph2
14	12,8	25,6	G14
15	19,2	25,6	Ph3
16	22,4	25,6	G16
17	32	25,6	ACIn1
18	25,6	19,2	ACIn2
19	19,2	16	Therm1
20	16	16	Therm2
21	25,6	12,8	ACIn3
22	22,4	6,4	DC+Inv
23	25,6	6,4	DC+Rect



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	600 V	20 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	600 V	20 A	Inverter Diode	
T27	IGBT	600 V	20 A	Brake Switch	
D27	FWD	600 V	10 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	28 A	Rectifier Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
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